

TO-252-2L Plastic-Encapsulate Transistors

KTA1042D TRANSISTOR (PNP)

FEATURES

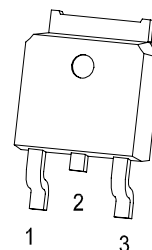
Low Collector-Emitter Saturation Voltage

APPLICATIONS

General Purpose Application

TO-252-2L

- 1. BASE
- 2. COLLECTOR
- 3. EMITTER



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-100	V
V _{CEO}	Collector-Emitter Voltage	-100	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-5	A
P _C	Collector Power Dissipation	1.25	W
R _{θJA}	Thermal Resistance from Junction to Ambient	100	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO} *	I _C =-1mA, I _E =0	-100			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C =-50mA, I _B =0	-100			V
Emitter-base breakdown voltage	V _{(BR)EBO} *	I _E =-1mA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-100V, I _E =0			-100	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-1	mA
DC current gain	h _{FE(1)}	V _{CE} =-5V, I _C =-1A	70		240	
	h _{FE(2)}	V _{CE} =-5V, I _C =-4A	20			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-4A, I _B =-0.4A			-2	V
Base-emitter voltage	V _{BE}	V _{CE} =-5V, I _C =-4A			-1.5	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-1A		30		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		270		pF

* Pulse test

CLASSIFICATION OF h_{FE(1)}

Rank	O	Y
Range	70-140	120-240

